

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-14 (Previously withdrawn).

- B²
15. (Currently amended) A silicon on insulator (SOI) semiconductor device comprising:
- a) a semiconductor body including a silicon supporting substrate, a silicon oxide layer supported by the substrate, and a silicon layer overlying the silicon oxide layer,
 - b) a semiconductor component formed in the silicon layer overlying a portion of the substrate in which silicon has been removed by etching, and
 - c) a metal layer in the portion of the substrate in which silicon has been removed by etching, the metal layer abutting the silicon oxide layer and providing heat removal from the component, the silicon oxide layer electrically insulating the metal layer from the semiconductor component.

Claims 16-20 (Previously cancelled).

21. (Previously amended) The semiconductor device as defined by claim 15, wherein the metal layer comprises a refractory metal.
22. (Previously amended) The semiconductor device as defined by claim 21, wherein the metal layer comprises gold, aluminum, or copper over the refractory metal.
23. (Original) The semiconductor device as defined by claim 21, wherein the refractory metal comprises titanium tungsten.